

SC12752TP

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Substitute for form 1449A/PTO				Complete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10687271
				Filing Date	October 16, 2003
				First Named Inventor	Olubunmi O. Adetutu et al.
				Group Art Unit	2813
				Examiner Name	Laura M. Schillinger
				Attorney Docket Number	SC12752TP
Sheet	1	of	1		

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Examiner Signature	<i>Walter Schulz</i>	Date Considered	1/22/06
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¹ Unique citation designation number. ² See *Kinds of U.S. Patent Documents*. ³ Enter *Ontio* that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of this year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbol as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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Substitute for form 1448A/PTO		Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10587,271	
		Filing Date	October 16, 2003	
		First Named Inventor	Olubunmi O. Adetutu et al.	
		Group Art Unit	2813	
		Examiner Name	Laura M. Schilling	
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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He	BH	Byeong-Ok Cho <i>et al.</i> , "Tuning the Electrical Properties of Zirconium Oxide Thin Films," <i>Applied Physics Letters</i> , February 11, 2002, Vol. 80, No. 6, pp. 1052-1054.	
I	BI	A. L. P. Rotondaro, <i>et al.</i> , "Advanced CMOS Transistors with a Novel HfSiON Gate Dielectric," <i>2002 Symposium on VLSI Technology Digest of Technical Papers</i> , Section 15.2.	
J	BJ	Yuji Saito, <i>et al.</i> , "Advantage of Radical Oxidation for Improving Reliability of Ultra-Thin Gate Oxide," <i>2002 Symposium on VLSI Technology Digest of Technical Papers</i> .	
Li	BK	M. Togo, <i>et al.</i> , "Low-Leakage and Highly-Reliable 1.5 nm SiON Gate-Dielectric Using Radical Oxynitridation for Sub-0.1 μ m CMOS," <i>2000 Symposium on VLSI Technology Digest of Technical Papers</i> .	

Examiner Signature	<i>Laura M. Schilling</i>	Date Considered	1/22/06
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		Application Number	10/687 271
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		First Named Inventor	Olubunmi O. Adetutu
		Group Art Unit	2813
Examiner Name			
Sheet 1 of 1	Attorney Docket Number	SC12752TP	

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number -Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

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AS	AA	Al-Shareef <i>et al.</i> , "Device Performance of <i>in-situ</i> Steam Generated Gate Dielectric Nitrided by Remote Plasma Nitridation," <i>Applied Physics Letters</i> , June 11, 2001, Vol. 78, No. 24, pp. 3875-3877/	
AS	AB	Nicollian <i>et al.</i> , "Extending Reliability Scaling Limit of SiO ₂ Through Plasma Nitridation," <i>IEDM Tech. Dig.</i> , 2000, pp. 545-548.	
AS	AC	Tseng <i>et al.</i> , "Ultra-Thin Decoupled Plasma Nitridation (DPN) Oxynitride Gate Dielectric for 80-nm Advanced Technology," <i>IEEE Electron Device Letters</i> , December 2002, Vol. 23, No. 12, pp. 704-706.	

Examiner Signature	Harsha Selvaraj	Date Considered	1/22/06
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